Charge Transport in Imperfect Organic Field Effect Transistors: Effects of Charge Traps

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Figures S1 shows the complete result of simulating I_{SD} as a function of the trap concentration while varying the seed percentage between 1% and 100% (homogeneous) for both traps and barriers. Figure S2 shows the simulated I_{SD} at 40% traps or barriers plotted as a function of the seed percentage.
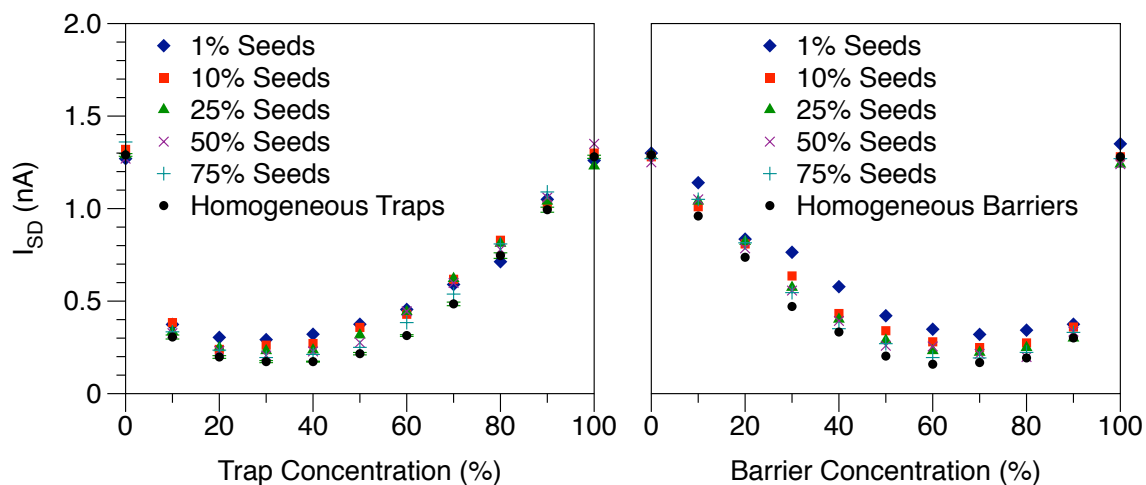

Figure S1: I_{SD} vs. trap concentration profiles at different seed percentages for traps (left) and barriers (right). $|\Delta\varepsilon| = 0.1$ eV
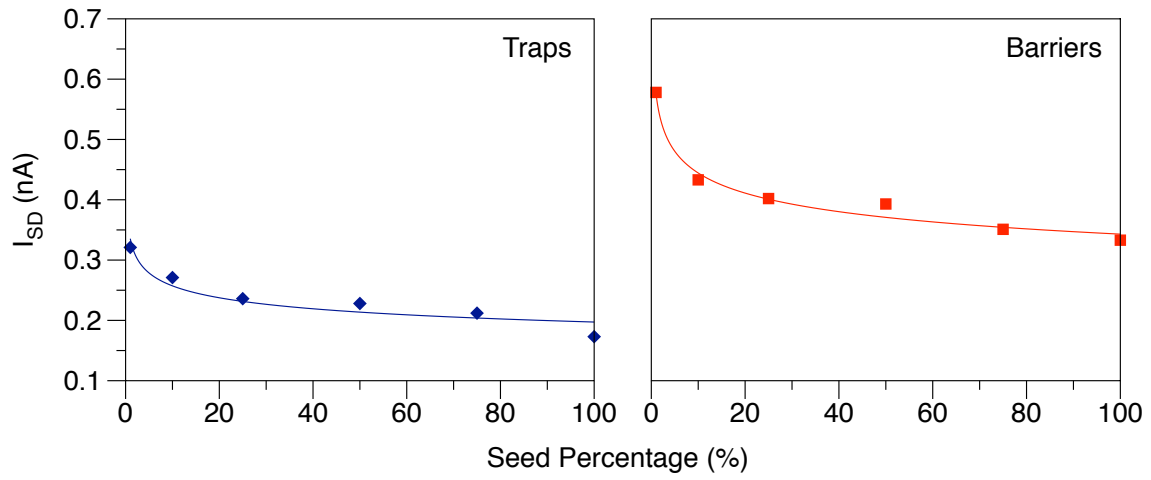
Figure S2: I_{SD} vs. seed percentage for traps (left) and barriers (right). 40% traps/barriers and $|\Delta\varepsilon| = 0.1$ eV.